

## 1. General description:

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.



## 2. Features and benefits:

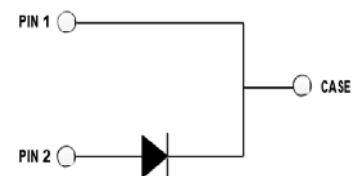
- Zero Reverse Recovery Current
- Positive temperature coefficient
- Temperature-independent performance
- High-speed switching
- Low switching loss
- Low heat dissipation requirements

## 3. Applications:

- Switching power supply
- Power factor correction
- Motor drive, traction
- Charging pile
- PC Silverbox

## 4. Typical Performance Diagrams and Package:

|                     |     |    |
|---------------------|-----|----|
| $V_{RRM}$           | 650 | V  |
| $I_F(110^{\circ}C)$ | 10  | A  |
| $Q_C$               | 28  | nC |



## 5. Ordering information:

| Parts Number  | Marking       | Package    | Vde min | IF max(A) | Pins | SPQ | Packaging |
|---------------|---------------|------------|---------|-----------|------|-----|-----------|
| TSSiC065S010F | TSSiC065S010F | TO-220F-2L | 650V    | 10A       | 2    | 600 | Tube      |
|               |               |            |         |           |      |     |           |

## Table of Contents

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|  |   |
|--|---|
| 1 Features .....                                 | 1 |
| 2 Applications .....                             | 1 |
| 3 Description .....                              | 1 |
| 4 Diagrams and Package .....                     | 1 |
| 5 Ordering information .....                     | 1 |
| 6 Table of Contents.....                         | 2 |
| 6 Absolute Maximum Ratings .....                 | 3 |
| 7 Thermal Characteristics.....                   | 3 |
| 8 Electrical Characteristics .....               | 3 |
| 9 Typical Electrical Characteristics Curves..... | 4 |
| 10 Package .....                                 | 5 |
| 11 Ordering information .....                    | 6 |
| 12 Notes .....                                   | 6 |

## 6. Absolute Maximum Ratings

| Parameter                            | Symbol        | Value   | Unit                 | Test Conditions   |
|--------------------------------------|---------------|---------|----------------------|---|
| Reverse voltage (Repetitive peak)    | $V_{RRM}$     | 650     | V                    | $T_C = 25^\circ\text{C}$  |
| Reverse Voltage (Surge peak)         | $V_{RSM}$     | 650     |                      | $T_C = 25^\circ\text{C}$  |
| Reverse voltage (DC)                 | $V_{DC}$      | 650     |                      | $T_C = 25^\circ\text{C}$  |
| Continuous forward current           | $I_F$         | 16      | A                    | $T_C = 25^\circ\text{C}$  |
|                                      |               | 10      |                      | $T_C = 110^\circ\text{C}$   |
| Surge non-repetitive forward current | $I_{FSM}$     | 80      | A                    | $T_C = 25^\circ\text{C}, t_p = 10\text{ms}, \text{half Sine Pulse}$ |
| Total power dissipation              | $P_{TOT}$     | 37.5    | W                    | $T_C = 25^\circ\text{C}$  |
| $i^2t$ value                         | $\int i^2 dt$ | 32      | $\text{A}^2\text{s}$ | $T_C = 25^\circ\text{C}, t_p = 10\text{ms}$                         |
| Operating temperature                | $T_j$         | -55~175 | $^\circ\text{C}$     |   |
| storage temperature                  | $T_{stg}$     | -55~175 | $^\circ\text{C}$     |   |
| Mounting Torque                      | M             | 1       | Nm                   | M3 Screw  |

## 7. Thermal Characteristics

| Parameter          | Symbol        | Values |      |      | Unit               | Test Condition |
|--------------------|---------------|--------|------|------|--------------------|----------------|
|                    |               | Min.   | Typ. | Max. |                    |                |
| Thermal resistance | $R_{th(j-c)}$ | /      | 4.0  | /    | $^\circ\text{C/W}$ |                |

## 8. Electrical Characteristics $T_j = 25^\circ\text{C}$

| Parameter                 | Symbol   | Values |      |      | Unit          | Test Condition                               |
|---------------------------|----------|--------|------|------|---------------|--|
|                           |          | Min.   | Typ. | Max. |               |  |
| DC blocking voltage       | $V_{DC}$ | 650    | /    | /    | V             | $I_R = 100 \mu\text{A}$                      |
| Forward voltage           | $V_F$    | /      | 1.45 | 1.70 | V             | $I_F = 10\text{A}, T_j = 25^\circ\text{C}$   |
|                           |          | /      | 1.75 | 2.50 |               | $I_F = 10\text{A}, T_j = 175^\circ\text{C}$  |
| Reverse current           | $I_R$    | /      | 1    | 40   | $\mu\text{A}$ | $V_R = 650\text{V}, T_j = 25^\circ\text{C}$  |
|                           |          | /      | 5    | 200  |               | $V_R = 650\text{V}, T_j = 175^\circ\text{C}$ |
| Total capacitance         | C        | /      | 534  | /    | pF            | $V_R = 0\text{V}, f = 1\text{MHz}$           |
|                           |          | /      | 53   | /    |               | $V_R = 200\text{V}, f = 1\text{MHz}$         |
|                           |          | /      | 46   | /    |               | $V_R = 400\text{V}, f = 1\text{MHz}$         |
| Total capacitive charge   | $Q_C$    | /      | 28   | /    | nC            | $V_R = 400\text{V}$                          |
| Capacitance Stored Energy | $E_C$    | /      | 4.3  | /    | $\mu\text{J}$ | $V_R = 400\text{V}$                          |

## 9. Typical Electrical Characteristics Curves

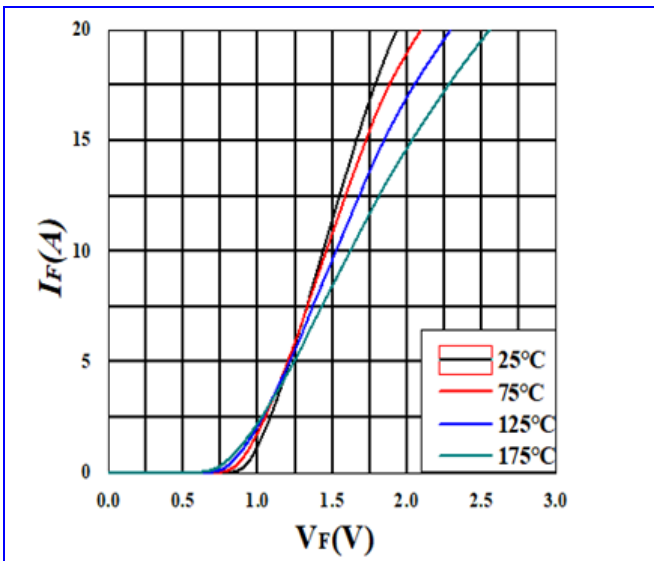


Figure 1. Forward Characteristics

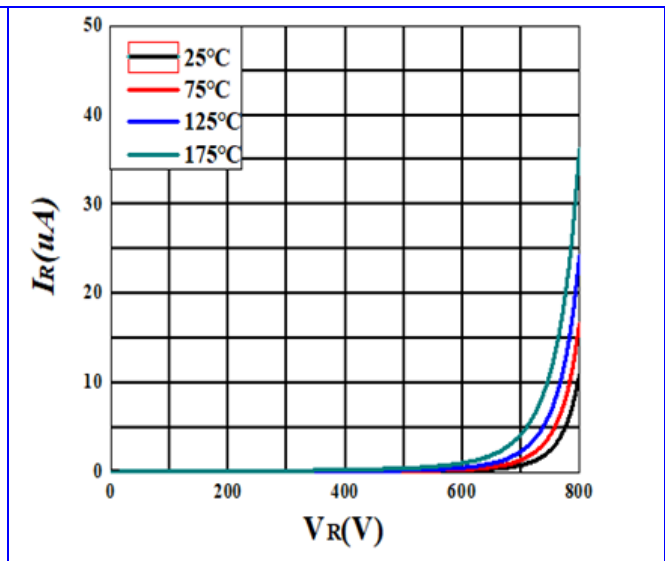


Figure 2. Reverse Characteristics

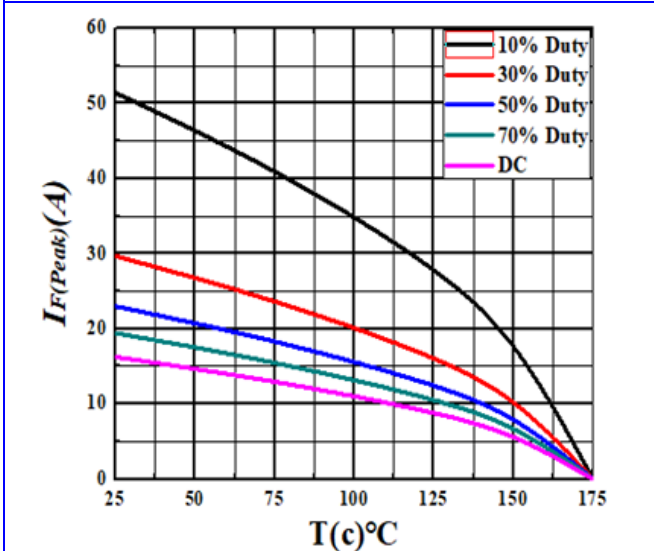


Figure 3. Current Derating

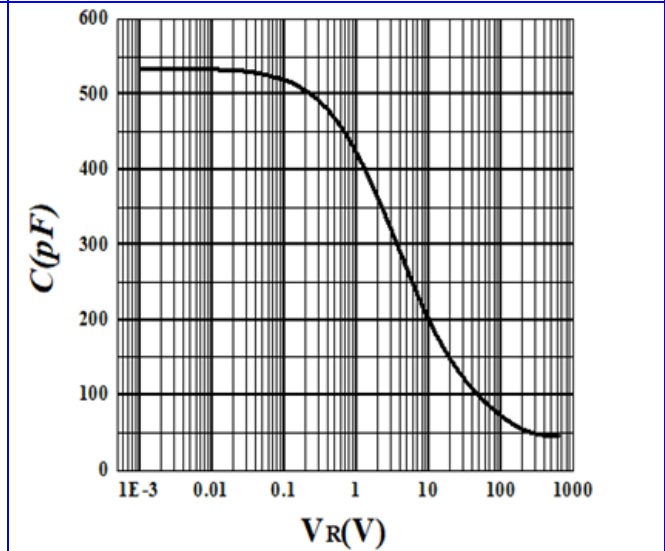


Figure 4. Capacitance vs. Reverse Voltage

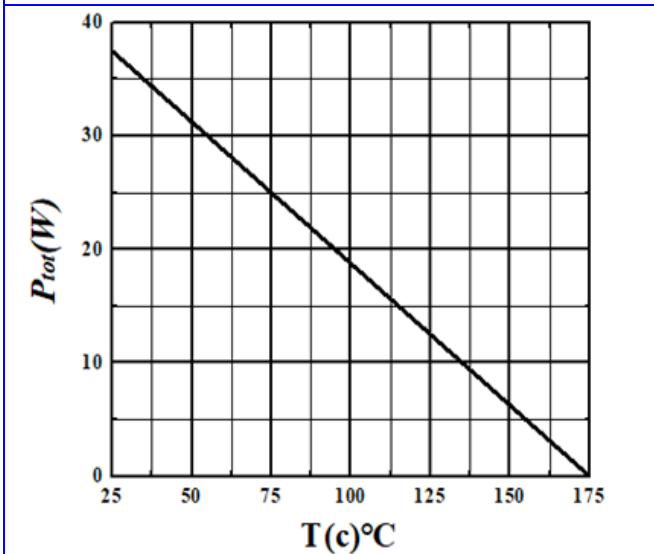


Figure 5. Power Derating

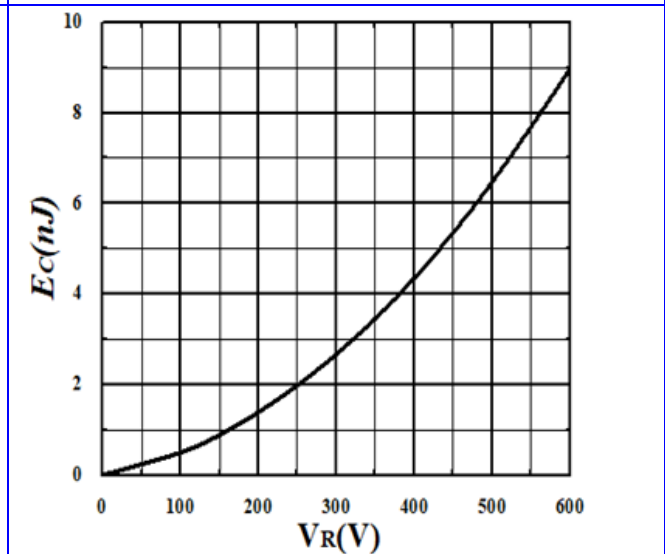


Figure 6. Capacitance Stored Energy

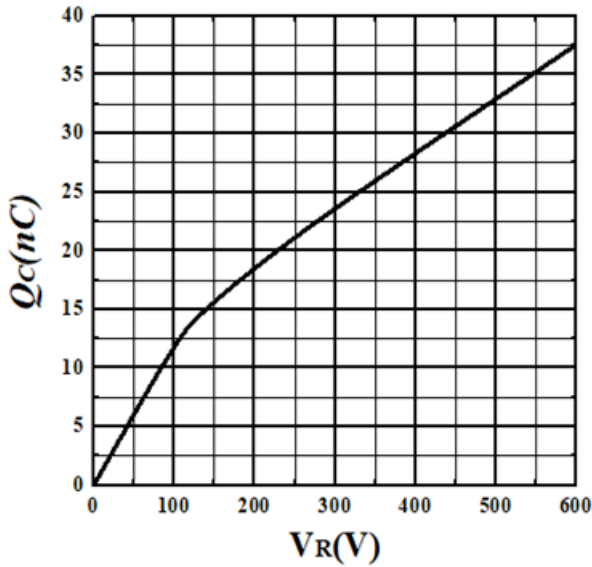
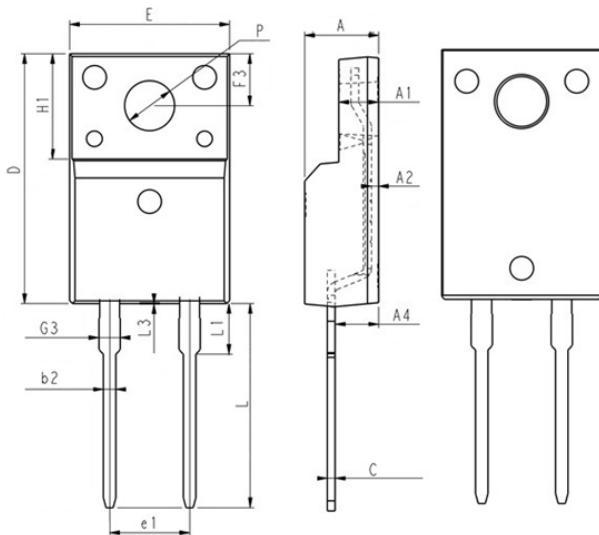


Figure 7. Total Capacitance Charge vs. Reverse Voltage

## 10. Package



| SYMBOL | mm       |       |       |
|--------|----------|-------|-------|
|        | MIN      | NOM   | MAX   |
| A      | 4.50     | 4.70  | 4.90  |
| A1     | 2.34     | 2.54  | 2.74  |
| A2     | 0.30     | 0.45  | 0.60  |
| A4     | 2.56     | 2.76  | 2.96  |
| b2     | 0.75     | 0.80  | 0.90  |
| C      | 0.45     | 0.50  | 0.60  |
| D      | 15.57    | 15.87 | 16.17 |
| E      | 9.96     | 10.16 | 10.36 |
| e1     | 5.08 BSC |       |       |
| F3     | 3.15     | 3.30  | 3.45  |
| G3     | 1.25     | 1.35  | 1.50  |
| H1     | 6.50     | 6.70  | 6.90  |
| L      | 12.68    | 12.98 | 13.28 |
| L1     | 3.08     | 3.23  | 3.38  |
| L3     | -        | -     | 0.20  |
| P dia. | 3.03     | 3.18  | 3.38  |

## 11. Ordering information

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|               |               |
|---------------|---------------|
| Part Number   | TSSiC065S010F |
| Package       | TO-220F-2L    |
| Marking       | TSSiC065S010F |
| Unit Quantity | 600 EA        |
| Packing Type  | Tube          |
| RoHS          | Yes           |

## 12. Notes

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SiC Schottky diode portfolio: <http://www.thrivesemi.com/>

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